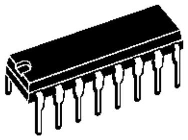
双 岭 上海双岭电子有限公司

CC4050

HEX BUFFER/CONVERTER (NON INVERTING)

- PROPAGATION DELAY TIME : t_{PD} = 40ns (TYP.) at V_{DD} = 10V C_L = 50pF
- HIGH TO LOW LEVEL LOGIC CONVERSION
- HIGH ”SINK” AND ”SOURCE” CURRENT CAPABILITY
- QUIESCENT CURRENT SPECIFIED UP TO 20V
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT LEAKAGE CURRENT I_I = 100nA (MAX) AT V_{DD} = 18V T_A = 25°C
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC JESD13B ” STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES”



DIP

ORDER CODES

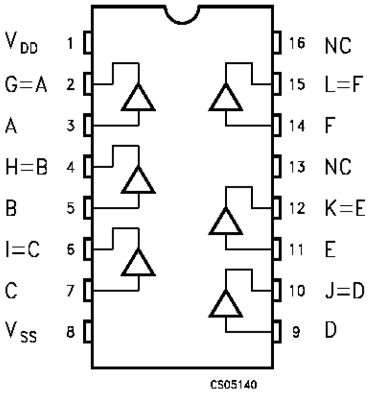
PACKAGE	TUBE	T & R
DIP	CC4050	

DESCRIPTION

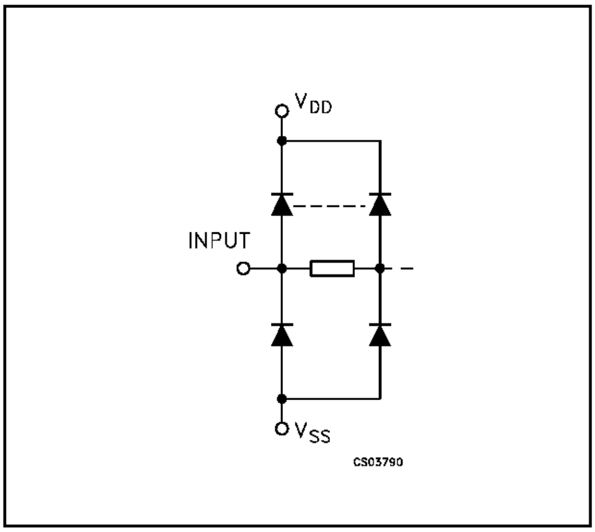
The CC4050 is a monolithic integrated circuit fabricated in Metal Oxide Semiconductor technology available in DIP and SOP packages. It is an non inverting Hex Buffer/Converter and feature logic level conversions using only one supply voltage (V_{DD}).

The input high level signal (V_{IH}) can exceed the V_{DD} supply voltage when these devices are used for logic level conversions. This device is intended for use as CMOS to DTL/TTL converters and can drive directly two DTL/TTL loads (V_{DD}=5V, V_{OL}≤0.4V and I_{OL}≤3.2mA.

PIN CONNECTION



INPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
3, 5, 7, 9, 11, 14	A, B, C, D, E, F	Data Inputs
2, 4, 6, 10, 12, 15	G, H, I, J, K, L	Data Outputs
13 , 16	NC	Not Connected
8	V_{SS}	Negative Supply Voltage
1	V_{DD}	Positive Supply Voltage

TRUTH TABLE

INPUTS	OUTPUTS
A, B, C, D,E, F	**G, H, I, J, K, L**
L	L
H	H

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage	-0.5 to +20	V
V_I	DC Input Voltage	-0.5 to V_{DD} + 0.5	V
I_I	DC Input Current	± 10	mA
P_D	Power Dissipation per Package	200	mW
	Power Dissipation per Output Transistor	100	mW
T_{op}	Operating Temperature	-55 to +125	°C
T_{stg}	Storage Temperature	-65 to +150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.
All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage	3 to 1 8	V
V_I	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature	-55 to 125	°C

DC SPECIFICATIONS

Symbol	Parameter	Test Condition				Value							Unit
		V_I (V)	V_O (V)	$\lvert I_O \rvert$ (μA)	V_{DD} (V)	T_A = 25°C			-40 to 85°C		-55 to 125°C		
						Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
I_L	Quiescent Current	0/5			5		0.02	1		30		30	μA
		0/10			10		0.02	2		60		60	
		0/15			15		0.02	4		120		120	
		0/18			18		0.04	20		600		600	
V_{OH}	High Level Output Voltage	0/5		<1	5	4.95			4.95		4.95		V
		0/10		<1	10	9.95			9.95		9.95		
		0/15		<1	15	14.95			14.95		14.95		
V_{OL}	Low Level Output Voltage	5/0		<1	5		0.05			0.05		0.05	V
		10/0		<1	10		0.05			0.05		0.05	
		15/0		<1	15		0.05			0.05		0.05	
V_{IH}	High Level Input Voltage		0.5/4.5	<1	5	3.5			3.5		3.5		V
			1/9	<1	10	7			7		7		
			1.5/13.5	<1	15	11			11		11		
V_{IL}	Low Level Input Voltage		4.5/0.5	<1	5			1.5		1.5		1.5	V
			9/1	<1	10			3		3		3	
			13.5/1.5	<1	15			4		4		4	
I_{OH}	Output Drive Current	0/5	2.5	<1	5	-1.25	-6.4		-0.42		-0.42		mA
		0/5	4.6	<1	5	-0.51	-1.6		-0.38		-0.38		
		0/10	9.5	<1	10	-1.25	-3.6		-1		-1		
		0/15	13.5	<1	15	-3.75	-12		-3		-3		
I_{OL}	Output Sink Current	0/5	0.4	<1	5	3.2	6.4		2.6		2.6		mA
		0/10	0.5	<1	10	8	16		6.6		6.6		
		0/15	1.5	<1	15	24	48		19		19		
I_I	Input Leakage Current	0/18	Any Input		18		$\pm 10^{-5}$	±0.1		±1		±1	μA
C_I	Input Capacitance		Any Input				5	7.5					pF

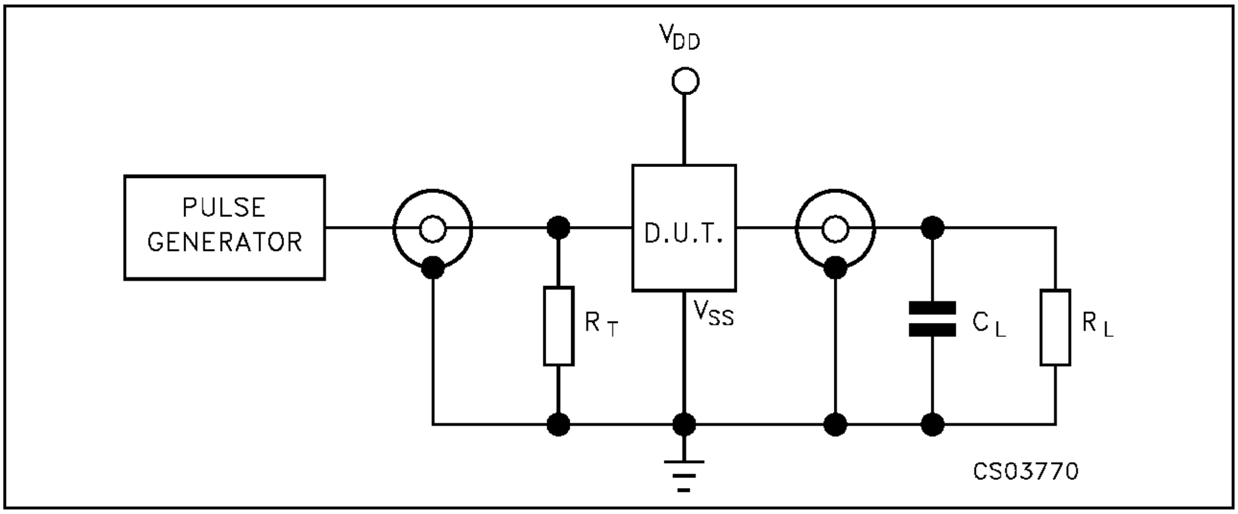
The Noise Margin for both "1" and "0" level is: 1V min. with V_{DD}=5V, 2V min. with V_{DD}=10V, 2.5V min. with V_{DD}=15V

DYNAMIC ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C, C_L = 50pF, R_L = 200KΩ, $t_r = t_f$ = 20 ns)

Symbol	Parameter	Test Condition			Value (*)			Unit
		V_{DD} (V)	V_I (V)		Min.	Typ.	Max.	
t_{TLH}	Output Transition Time	5	5			80	160	ns
		10	10			40	80	
		15	15			30	60	
t_{THL}	Output Transition Time	5	5			30	60	ns
		10	10			20	40	
		15	15			15	30	
t_{PLH}	Propagation Delay Time	5	5			70	140	ns
		10	10			40	80	
		5	10			45	90	
		15	15			30	60	
		5	15			40	80	
t_{PHL}	Propagation Delay Time	5	5			55	110	ns
		10	10			22	55	
		5	10			50	100	
		15	15			15	30	
		5	15			50	100	

(*) Typical temperature coefficient for all V_{DD} value is 0.3 %/°C.

TEST CIRCUIT



C_L = 50pF or equivalent (includes jig and probe capacitance)
R_L = 200KΩ
R_T = Z_{OUT} of pulse generator (typically 50Ω)